

FQPF2N80YDTU

N-Channel QFET® MOSFET

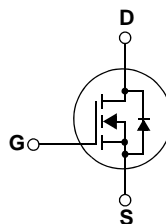
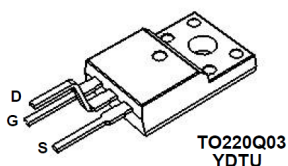
80 V, 1.5 A, 8 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 1.5 A, 80 V, $R_{DS(on)} = 8 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 0.75 \text{ A}$
- Low Gate Charge (Typ. 12 nC)
- Low C_{rss} (Typ. 5.5 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQPF2N80YDTU	Unit
V_{DSS}	Drain-Source Voltage	800	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	1.5	A
		0.95	A
I_{DM}	Drain Current - Pulsed (Note 1)	6.0	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	5.2	mJ
I_{AR}	Avalanche Current (Note 1)	1.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	3.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	35	W
		0.28	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQPF2N80YDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.57	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	800	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.9	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.75\text{ A}$	--	4.9	6.3	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.75\text{ A}$	--	2.2	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	425	550	pF
C_{oss}	Output Capacitance		--	45	60	pF
C_{riss}	Reverse Transfer Capacitance		--	5.5	7.0	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 2.4\text{ A}, R_G = 25\ \Omega$	--	12	35	ns	
t_r	Turn-On Rise Time		--	30	70	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	25	60	ns
t_f	Turn-Off Fall Time		(Note 4)	--	28	65	ns
Q_g	Total Gate Charge	$V_{DS} = 640\text{ V}, I_D = 2.4\text{ A}, V_{GS} = 10\text{ V}$	--	12	15	nC	
Q_{gs}	Gate-Source Charge		(Note 4)	--	2.6	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	6.0	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.5	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	6.0	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.5\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 2.4\text{ A}, di_F / dt = 100\text{ A}/\mu\text{s}$	--	480	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.0	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 4.3\text{ mH}, I_{AS} = 1.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 2.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

Typical Characteristics

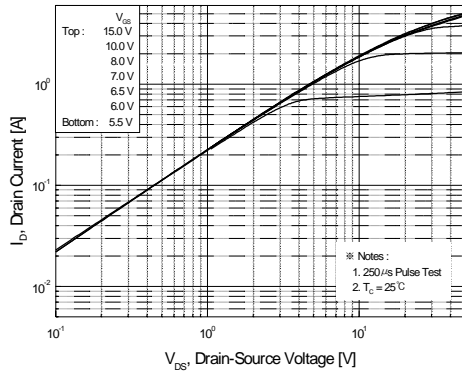


Figure 1. On-Region Characteristics

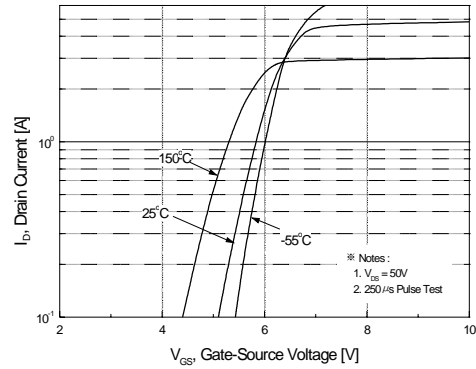


Figure 2. Transfer Characteristics

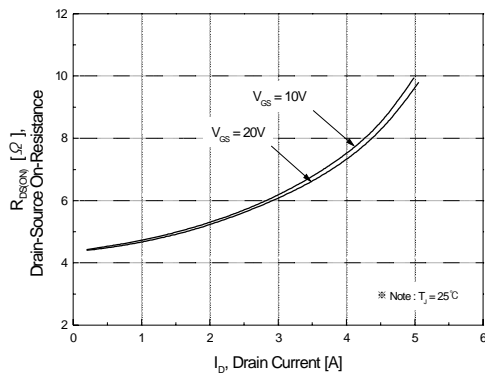


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

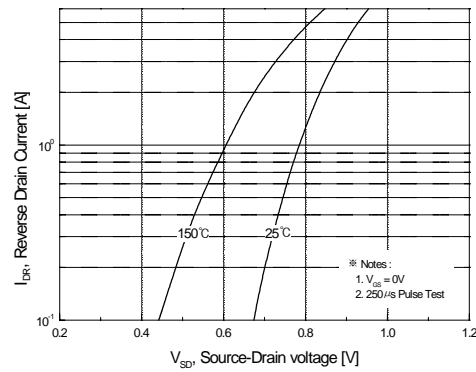


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

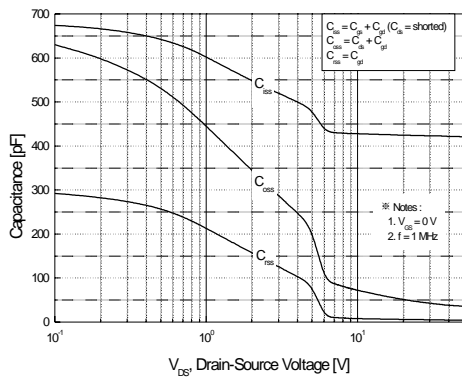


Figure 5. Capacitance Characteristics

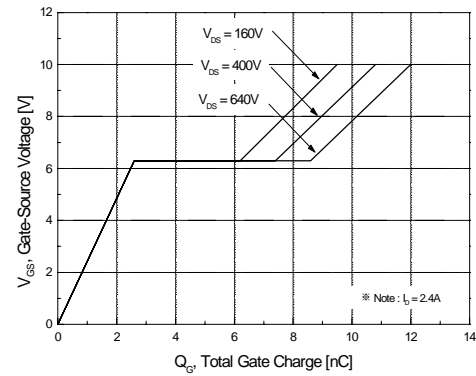


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

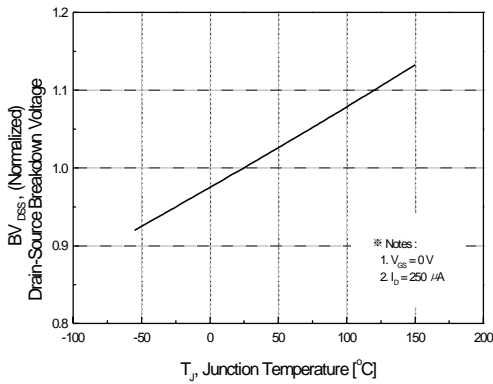


Figure 7. Breakdown Voltage Variation vs Temperature

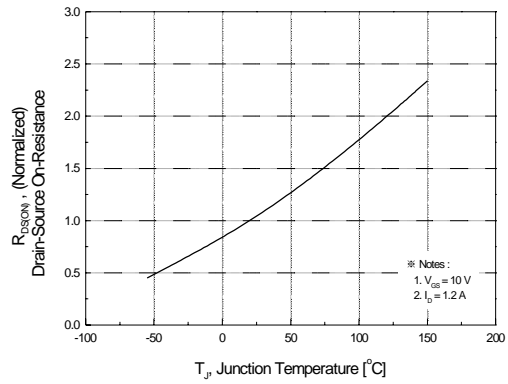


Figure 8. On-Resistance Variation vs Temperature

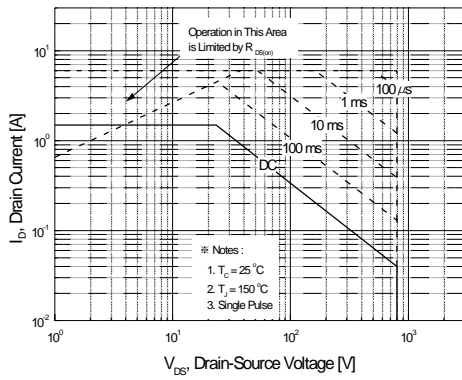


Figure 9. Maximum Safe Operating Area

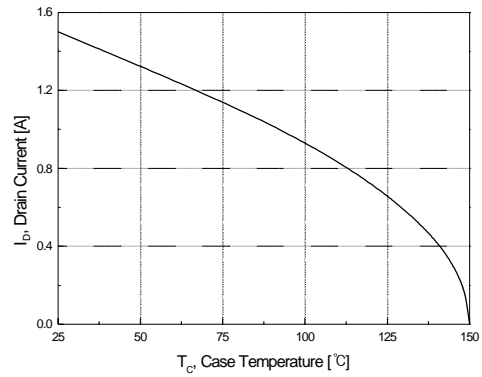


Figure 10. Maximum Drain Current vs Case Temperature

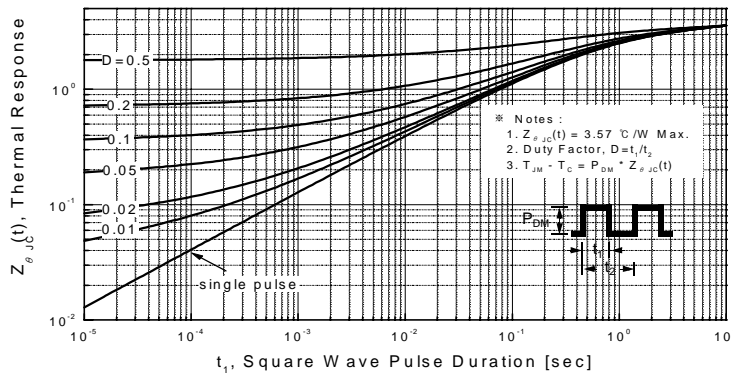
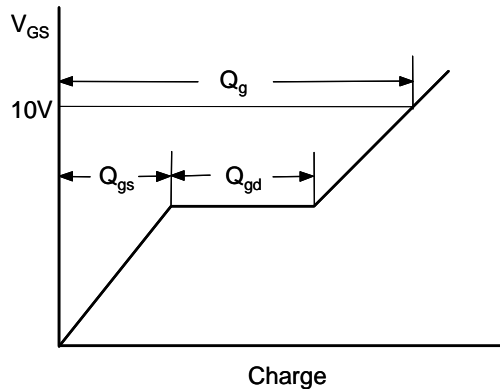
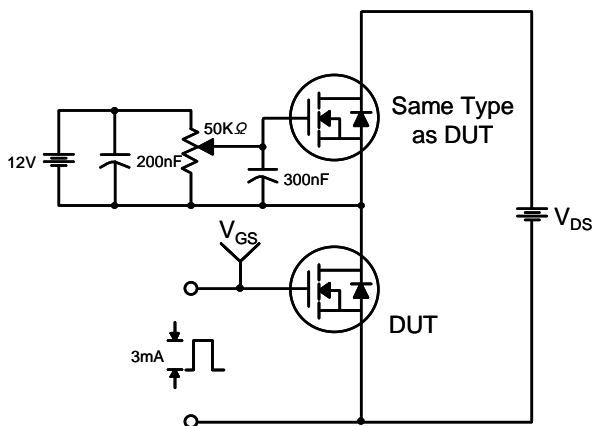
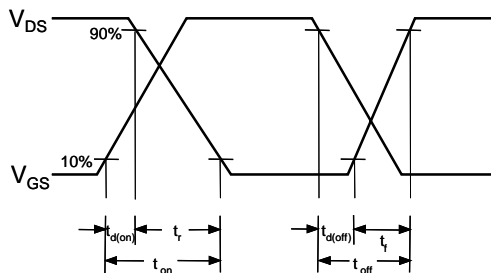
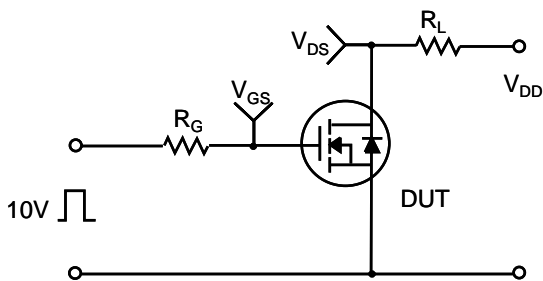


Figure 11. Transient Thermal Response Curve

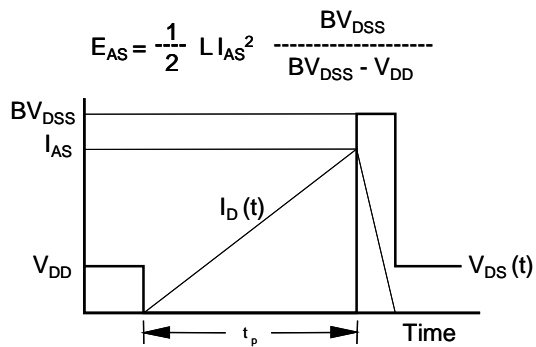
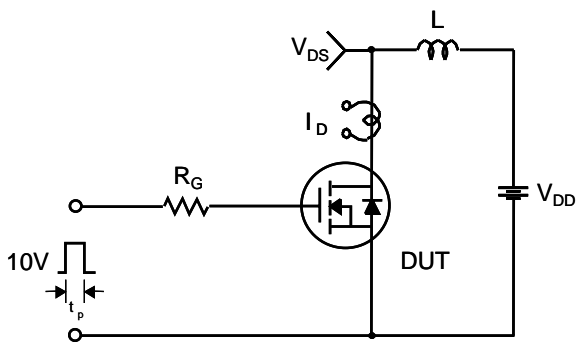
Gate Charge Test Circuit & Waveform



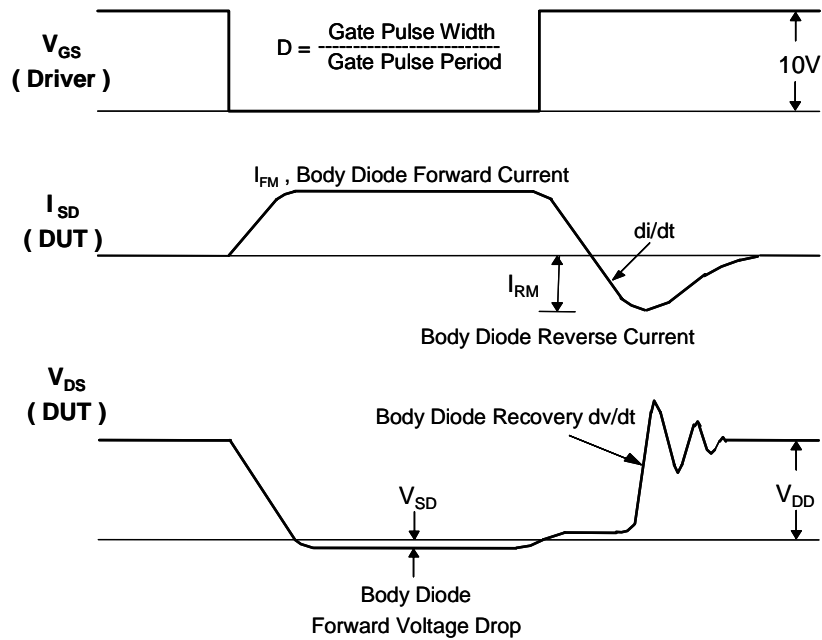
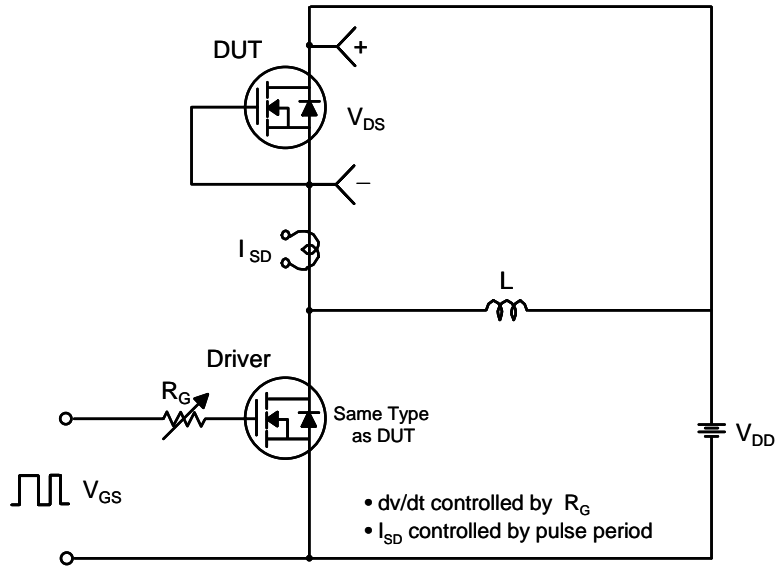
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

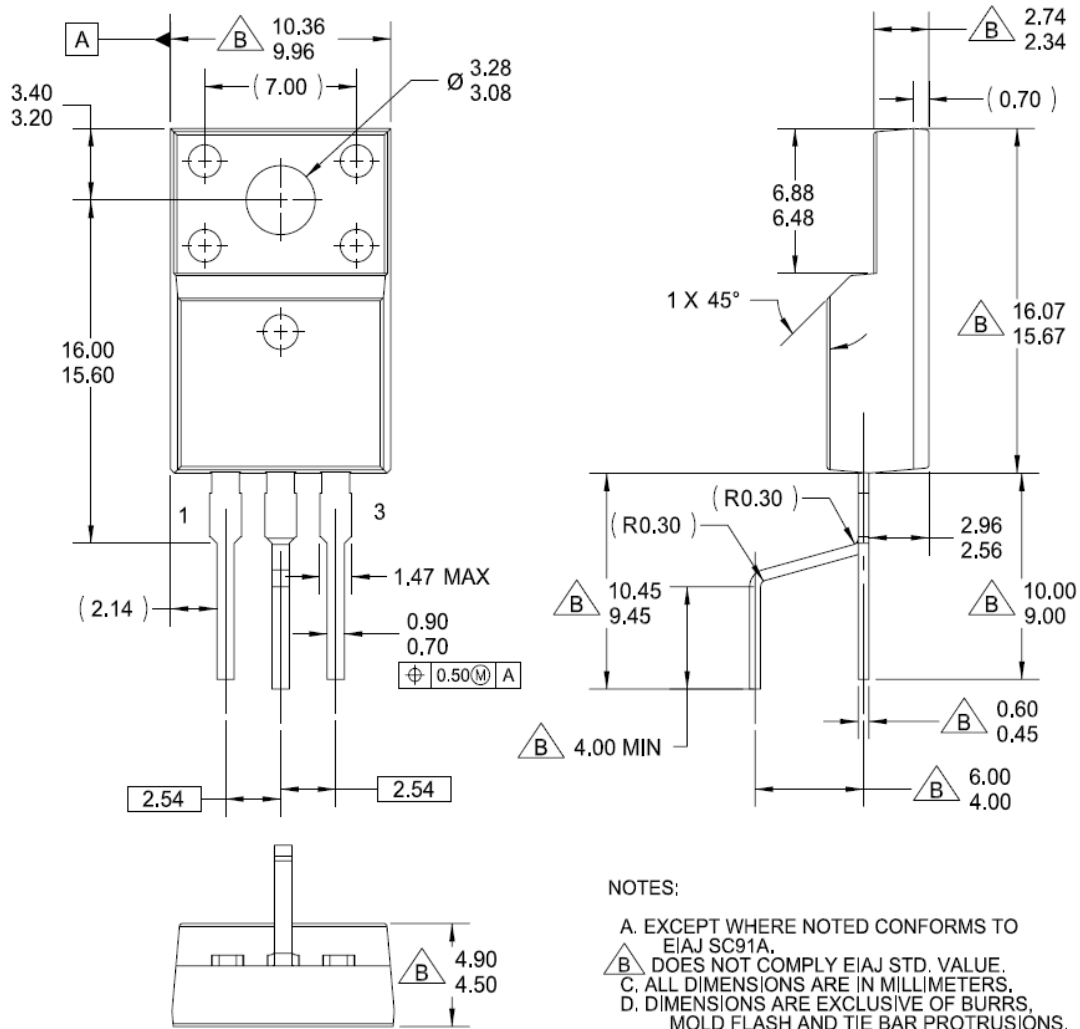


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO220Q03



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- $\triangle B$. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. DRAWING FILE NAME: TO220Q03REV1

TO-220F 3L - TO220, MOLDED, 3LD, FULL PACK, EIAJ SC91, Y FORMED LEAD

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-FA3

Dimensions in Millimeters

